

REMARKS

Claims 1-21 and 23-38 are pending, with claims 1-3, 10, 11, 16-20 and 23-25 being independent. Claims 10, 12-14, 16-21, 23-25, 29 and 31-35 have been withdrawn, leaving claims 1-9, 11, 15, 26-28, 30 and 36-38 under consideration, with claims 1-3 and 11 being independent. Claims 1-3 have been amended and claims 36-38 have been added. Support for the amendments to claims 1 and 2 may be found in the application at, for example, page 20, line 28 to page 21, line 2, and support for the amendments to claim 3 may be found in the application at, for example, page 21, line 26 to page 22, line 2. Support for new claims 36-38 may be found at page 32, lines 20-22. No new matter has been introduced.

Applicant acknowledges with appreciation the Examiner's allowance of claims 11, 13, 15 and 30.

Claims 1, 2, 4, 5, 26 and 27 have been rejected as being anticipated by Toida (JP05-243262). Applicant requests reconsideration and withdrawal of this rejection because Toida does not describe or suggest a semiconductor layer formed over a substrate having an insulating surface, as recited in each of amended independent claims 1 and 2. Rather, Toida, at paragraph [0006], states that the gate electrode 35 and the low concentration field 29 are formed in the semiconductor substrate 11. Thus, Toida does not disclose a substrate having an insulating surface and a semiconductor layer formed over the substrate, and the rejection should be withdrawn for at least this reason.

Claims 7 and 8 have been rejected as being unpatentable over Toida in view of JP 6-148685 (the '685 reference). Applicant requests reconsideration and withdrawal of this rejection because the '685 reference does not remedy the failure of Toida to describe or suggest the subject matter of the independent claims from which claims 7 and 8 depend.

Claims 3, 6 and 28 have been rejected as being unpatentable over Toida in view of Nishimura (U.S. Patent No. 6,462,802). Applicant requests reconsideration and withdrawal of this rejection because neither Toida, Nishimura, nor any proper combination of the two describes or suggests a gate insulating film having a first thickness in a region where the gate insulating

Applicant : Shunpei YAMAZAKI et al.
Serial No. : 09/809,646
Filed : March 16, 2001
Page : 18 of 18

Attorney's Docket No.: 12732-021001 / US4802

film is covered by a first gate electrode and a second thickness in a region where the gate insulating film is not covered by the first gate electrode, with the second thickness being thinner than the first thickness, as recited in claim 3.

Claim 9 has been rejected as being unpatentable over Toida in view of Nishimura and the '685 reference. Applicant requests reconsideration and withdrawal of this rejection because the '685 reference does not remedy the failure of Toida and Nishimura to describe or suggest the subject matter of independent claim 3 from which claim 9 depends.

Applicant submits that all claims are in condition for allowance.


A check for \$910 for the Request for Continued Examination fee and One-Month Extension of time fee is enclosed. Please apply any other charges or credits to deposit account 06-1050.

Respectfully submitted,

Date: _____

9/13/05

Customer No. 26171
Fish & Richardson P.C.
1425 K Street, N.W. - 11th Floor
Washington, DC 20005-3500
Telephone: (202) 783-5070
Facsimile: (202) 783-2331
/adt
40285711.doc



John F. Hayden
Reg. No. 37,640